

Description

The IRFR5505PbF uses advanced trench technology

to provide excellent $\mathsf{R}_{\mathsf{DS}(\mathsf{ON})},$ low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = -60V I_D =-15 A

 $R_{DS(ON)} < 82m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

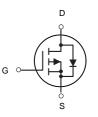
Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR5505PbF	TO-252-2L	HXY MOSFET	2500

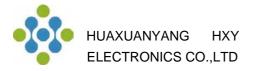
Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Rating	Units	
VDS	Drain-Source Voltage	-60	V	
Vgs	Gate-Source Voltage	±20	V	
I₀@Tc=25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-15	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-11	А	
I₀@T _A =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-4.3	А	
ID@TA=70°C	Continuous Drain Current, V _{GS} @ -10V ¹	/ _{GS} @ -10V ¹ -3.5		
Ідм	Pulsed Drain Current ²	-36	А	
EAS	Single Pulse Avalanche Energy ³	35.4	mJ	
las	Avalanche Current	-26.6	А	
P₀@Tc=25°C	Total Power Dissipation ⁴	34.7	W	
PD@TA=25°C	Total Power Dissipation ⁴	2	W	
Тятд	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R _{0JA}	Thermal Resistance Junction-Ambient ¹	62	°C/W	
Rejc	Thermal Resistance Junction-Case ¹	3.6	°C/W	





P-Channel MOSFET



Electrical Characteristics (T_A=25°Cunless otherwise noted)

Symbol	nbol Parameter Conditions		Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
∆Bvoss /∆Tj	BV _{DSS} Temperature Coefficient	Reference to 25° C , I _D =-1mA		-0.03		V/℃
		V _{GS} =-10V , I _D =-12A		70	82	
RDS(ON)	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-8A		85	105	mΩ
VGS(th)	Gate Threshold Voltage		-1.2	1.5	-2.5	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250uA		4.56		mV/°(
		$V_{\text{DS}}\text{=-48V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathbb{C}$			1	
loss	Drain-Source Leakage Current V _{DS} =-48V , V _{GS} =0V , T _J =55°C				5	uA
lgss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-12A		15.4		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13.5		Ω
Qg	Total Gate Charge (-4.5V)			9.86		
Qgs	Gate-Source Charge	V _{DS} =-48V , V _{GS} =-4.5V , I _D =-10A		3.08		nC
Q _{gd}	Gate-Drain Charge			2.95		
Td(on)	Turn-On Delay Time			28.8		
Tr	Rise Time	V _{DD} =-15V , V _{GS} =-10V ,		19.8		
Td(off)	Turn-Off Delay Time	- R _G =3.3□, I _D =-1A		60.8		ns
T _f	Fall Time			7.2		
Ciss	Input Capacitance			1447		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		97.3		pF
Crss	Reverse Transfer Capacitance			70		
Is	Continuous Source Current ^{1,5}				-18	А
lsм	Pulsed Source Current ^{2,5}	$V_G=V_D=0V$, Force Current			-36	Α
Vsd	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , TJ=25℃			-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq\,$ 300us , duty cycle $\leq\,$ 2%

3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-26.6A

4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



IRFR5505PbF P-Channel Enhancement Mode MOSFET

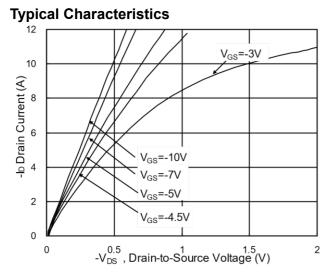


Fig.1 Typical Output Characteristics

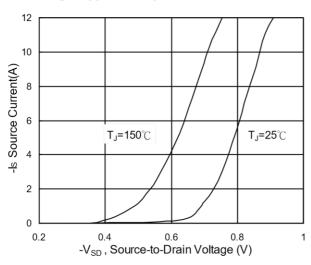
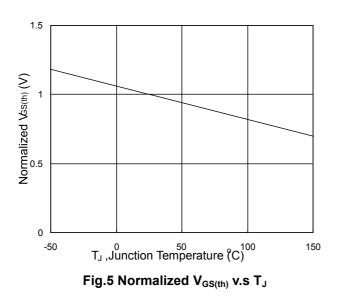


Fig.3 Forward Characteristics of Reverse



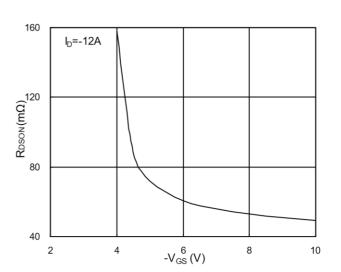


Fig.2 On-Resistance v.s Gate-Source

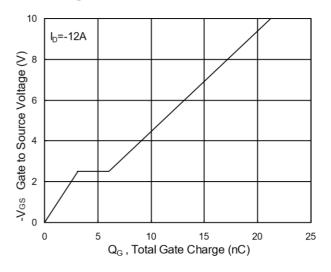
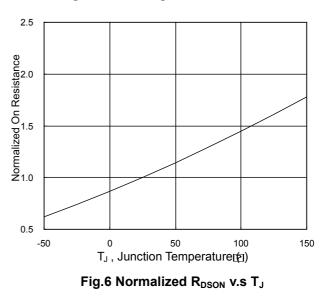


Fig.4 Gate-Charge Characteristics





IRFR5505PbF

P-Channel Enhancement Mode MOSFET

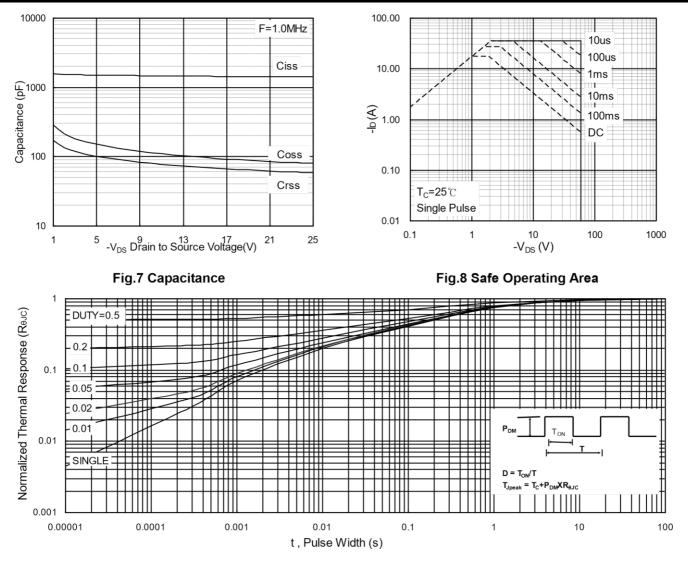


Fig.9 Normalized Maximum Transient Thermal Impedance

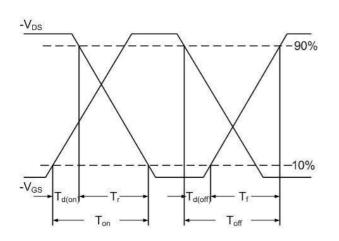
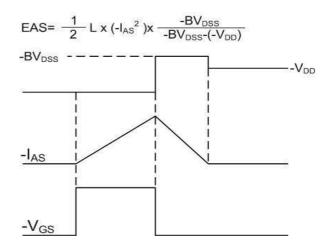


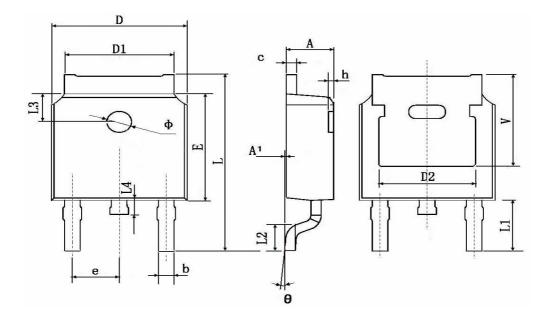
Fig.10 Switching Time Waveform







TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
e	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP. 0.211 TYP.		TYP.		



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